

ST1S30

3 A, 1.5 MHz PWM step-down switching regulator with synchronous rectification

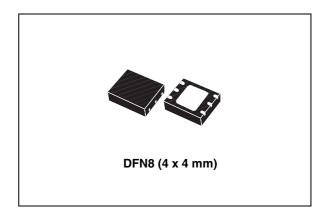
Features

- 1.5 MHz fixed frequency PWM with current control mode
- 3 A output current capability
- Typical efficiency: > 90%
- 2 % DC output voltage tolerance
- Two versions available: power good or inhibit
- Integrated output over-voltage protection
- Non switching quiescent current: (typ) 1.5 mA over temperature range
- \blacksquare R_{DSon} (typ) 100 mΩ
- Utilizes tiny capacitors and inductors
- Operating junction temp. -25 °C to 125 °C
- Available in DFN8 (4 x 4 mm) exposed pad

Description

The ST1S30 is a step-down DC-DC converter optimized for powering low output voltage applications. It supplies a current in excess of 3 A over an input voltage range from 2.7 V to 6 V.

A high PWM switching frequency (1.5 MHz) allows the use of tiny surface-mount components.



Moreover, since the required synchronous rectifier is integrated, the number of the external components is reduced to minimum: a resistor divider, an inductor and two capacitors. The Power Good function continuously monitors the output voltage. An open drain Power Good flag is released when the output voltage is within regulation. In addition, a low output ripple is guaranteed by the current mode PWM topology and by the use of low ESR SMD ceramic capacitors. The device is thermally protected and the output current limited to prevent damages due to accidental short circuit. The ST1S30 is available in the DFN8 (4 x 4 mm) package.

Table 1. Device summary

Order codes	Package	Note	
ST1S30PUR ⁽¹⁾	DFN8 (4 x 4 mm)	PG version	
ST1S30IPUR	DENO (4 X 4 IIIIII)	INHIBIT version	

^{1.} Available on request.

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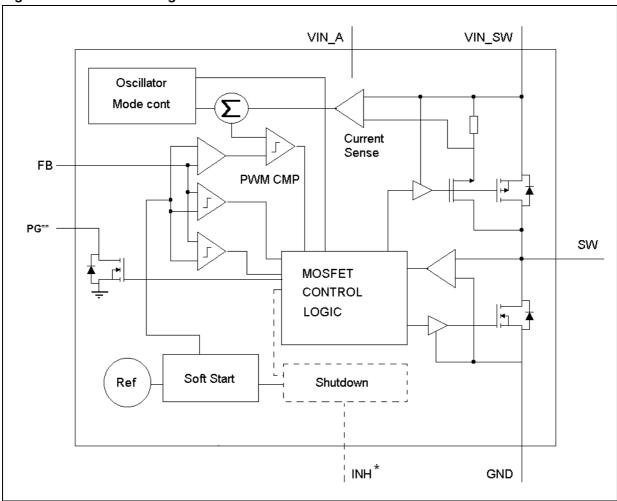
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ST1S30 Diagram

1 Diagram

Figure 1. Schematic diagram



(*) Only for ST1S30I

(**) Only for ST1S30

Pin configuration ST1S30

2 Pin configuration

Figure 2. Pin connections (top view)

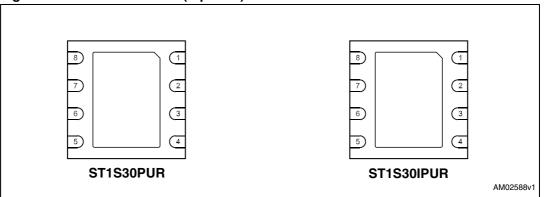


Table 2. Pin description

Pin n°	Symbol	Name and function
1	FB	Feedback voltage
2	GND	System ground
3	SW	Switching pin
6	V _{IN_SW}	Power supply for the MOSFET switch
7	V _{IN_A}	Power supply for analog circuit
8	INH/PG	Inhibit (INH) for ST1S30IPUR or Power Good (PG) for ST1S30PUR
Exposed pad	GND	To be connected to PCB ground plane for optimal electrical and thermal performance
4, 5	NC	Not internally connected. Can be connected to GND or left floating

ST1S30 Maximum ratings

3 Maximum ratings

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{IN_SW}	Positive power supply voltage	-0.3 to 7	V
V _{IN_A}	Positive power supply voltage	-0.3 to 7	V
V _{INH}	Inhibit voltage (I version)	-0.3 to V _I + 0.3	V
SWITCH voltage	Max. voltage of output pin	-0.3 to 7	٧
V _{FB}	Feedback voltage	-0.3 to 3	V
PG	Power Good open drain	-0.3 to 7	٧
T _J	Max junction temperature	-40 to 150	°C
T _{STG}	Storage temperature range	-65 to 150	°C
T _{LEAD}	Lead temperature (soldering) 10 sec	260	°C

Note:

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 4. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case	10	°C/W
R _{thJA}	Thermal resistance junction-ambient	40	°C/W

Table 5. ESD performance

Symbol	Parameter	Test conditions	Value	Unit
ESD	ESD protection voltage	НВМ	2	kV
ESD	ESD protection voltage	MM	500	V

Electrical characteristics ST1S30

4 Electrical characteristics

Refer to *Figure 3* application circuit $V_{IN_SW}=V_{IN_A}=5$ V, $V_O=1.2$ V, C1 = 10 μ F, $C_2=22~\mu$ F, L1 = 2.2 μ H, $T_J=-25$ to 125 °C (unless otherwise specified. Typical values are referred to 25 °C)

Table 6. Electrical characteristics for ST1S30

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
FB	Feedback voltage		784	800	816	mV	
I _{FB}	V _{FB} pin bias current				600	nA	
V _I	Input voltage	I _O = 10 mA to 3 A	2.7		5.5	V	
111/	Under voltage lock out	V _I Rising		2.3		V	
UV _{LO}	threshold	Hysteresis		150		mV	
OVP	Overvoltage protection threshold	V _O rising	1.05 V _O	1.1 V _O		V	
OVF	Overvoltage protection hysteresis	V _O falling		5		%	
I _{OVP}	Overvoltage clamping current	V _O = 1.2 V		300		mA	
1-	Quiescent current	V _{INH} > 1.2 V, not switching		1.5	2.5	mΛ	
ΙQ	Quiescent current	V _{INH} < 0.0 V, T = - 30 °C to 85 °C			1	– mA	
I _O	Output current	$V_1 = 2.7 \text{ to } 5.5 \text{ V}^{(1)}$	3			Α	
%V _O /ΔV _I	Output line regulation	$V_I = 2.7 \text{ V to } 5.5 \text{ V}, I_O = 100 \text{ mA}^{(1)}$		0.16		%V _O / ΔV _I	
%V _O /∆I _O	Output load regulation	$I_O = 10$ mA to 3 A $^{(1)}$		0.2		%	
PWMf _S	PWM switching frequency	V _{FB} = 0.65 V	1.2	1.5	1.8	MHz	
D _{MAX}	Maximum duty cycle		80	87		%	
PG	Power good output threshold			0.92 V _O		V	
1 4	Power good output voltage low	I _{SINK} = 6 mA open drain output			0.4	V	
R _{DSON} -N	NMOS switch on resistance	I _{SW} = 750 mA		0.1		Ω	
R _{DSON} -P	PMOS switch on resistance	I _{SW} = 750 mA		0.1		Ω	
I _{SWL}	Switching current limitation	(1)	3.7	4.4	5.1	Α	
N,	Efficiency ⁽¹⁾	$I_O = 10 \text{ mA to } 100 \text{ mA}, V_O = 3.3 \text{ V}$	65			%	
ν	Linciency ()	$I_O = 100 \text{ mA to } 3 \text{ A}, V_O = 3.3 \text{ V}$		85		/6	
T _{SHDN}	Thermal shutdown			150		°C	
T _{HYS}	Thermal shutdown hysteresis			20		°C	
%V _O /∆I _O	Load transient response	I_O = 100 mA to 1 A, T_A = 25 °C t_R = t_F \geq 200 ns ⁽¹⁾	-10		+10	%V _O	
%V _O /∆I _O	Short circuit removal response	I_O = 10 mA to I_O = short, T_A = 25 °C ⁽¹⁾	-10		+10	%V _O	

^{1.} Guaranteed by design, but not tested in production.

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Refer to Figure 4 application circuit $V_{IN_SW}=V_{IN_A}=V_{INH}=5$ V, $V_O=1.2$ V, C1 = 10 μ F, C2 = 22, C3 = 1 μ F, L1 = 2.2 μ H, $T_J=-25$ to 125 °C (unless otherwise specified. Typical values are referred to 25 °C)

Table 7. Electrical characteristics for ST1S30I

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
FB	Feedback voltage		784	800	816	mV
I _{FB}	V _{FB} pin bias current				600	nA
VI	Minimum input voltage	I _O = 10 mA to 2 A	2.7			٧
OVP	Overvoltage protection threshold	V _O rising	1.05 V _O	1.1 V _O		٧
OVI	Overvoltage protection hysteresis	V _O falling		5		%
la	Quiescent current	V _{INH} > 1.2 V, not switching		1.5	2.5	mA
ΙQ	Quiescent current	V_{INH} < 0.0 V, T = - 30 °C to 85 °C			1	μΑ
Io	Output current	$V_1 = 2.7 \text{ to } 5.5 \text{ V}^{(1)}$	3			Α
		Device ON, V _I = 2.7 to 5.5 V	1.3			
V _{INH}	Inhibit threshold	Device ON, V _I = 2.7 to 5 V	1.2			V
		Device OFF			0.4	
I _{INH}	Inhibit pin current				2	μΑ
%V _O /ΔV _I	Output line regulation	$V_{I} = 2.7 \text{ V to } 5.5 \text{ V}, I_{O} = 100 \text{ mA}^{(1)}$		0.16		%V _O / ΔV _I
%V _O /∆I _O	Output load regulation	I _O = 10 mA to 2 A ⁽¹⁾		0.2	0.6	%V _O / ∆I _O
PWMf _S	PWM switching frequency	V _{FB} = 0.65 V	1.2	1.5	1.8	MHz
D _{MAX}	Maximum duty cycle		80	87		%
R _{DSON} -N	NMOS switch on resistance	I _{SW} = 750 mA		0.1		Ω
R _{DSON} -P	PMOS switch on resistance	I _{SW} = 750 mA		0.1		Ω
I _{SWL}	Switching current limitation	(1)	3.7	4.4	5.1	Α
v	Efficiency (1)	$I_O = 10 \text{ mA to } 100 \text{ mA}, V_O = 3.3 \text{ V}$	65			%
V	Efficiency	I _O = 100 mA to 3 A, V _O = 3.3 V		85		70
T _{SHDN}	Thermal shutdown			150		°C
T _{HYS}	Thermal shutdown hysteresis			20		°C
%V _O /∆I _O	Load transient response	I_O = 100 mA to 1 A, T_A = 25 °C t_R = t_F \geq 200 ns ⁽¹⁾	-10		+10	%V _O
%V _O /∆I _O	Short circuit removal response	$I_O = 10$ mA to $I_O =$ short, $T_A = 25$ °C ⁽¹⁾	-10		+10	%V _O

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5 Typical application circuits

Figure 3. Application circuit fot $V_{OUT} > 1.2 \text{ V}$

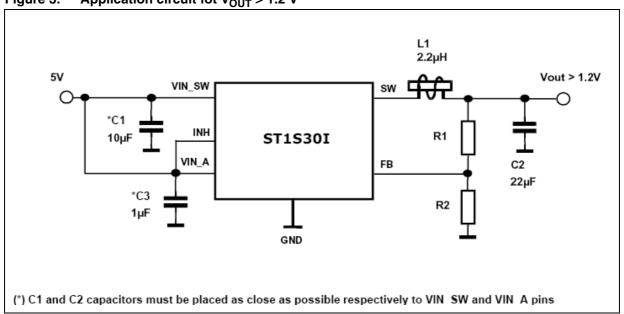
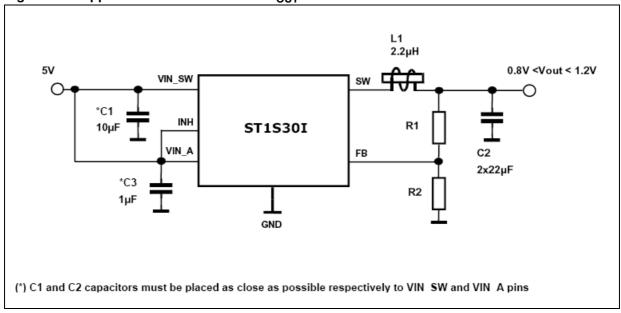


Figure 4. Application circuit for $0.8 \text{ V} < V_{OUT} < 1.2 \text{ V}$



Note:

These typical application circuits are provided to help designing the external components. However, we recommend to thoroughly validate any circuit solution in the real application environment conditions.

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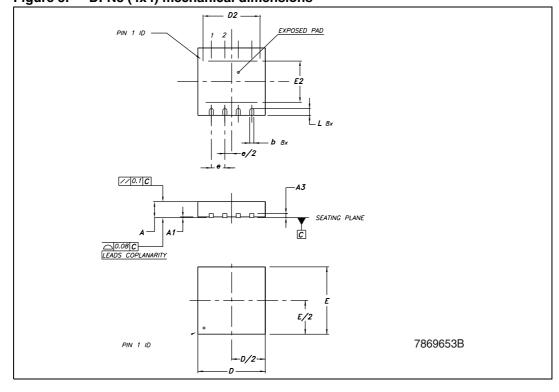
6 Package mechanical data

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Table 8.	DFN8 ((4x4)	mechanical	data

Dim.		mm.	
Dilli.	Min.	Тур.	Max.
Α	0.80	0.90	1.00
A1	0	0.02	0.05
A3		0.20	
b	0.23	0.30	0.38
D	3.90	4.00	4.10
D2	2.82	3.00	3.23
E	3.90	4.00	4.10
E2	2.05	2.20	2.30
е		0.80	
L	0.40	0.50	0.60

Figure 5. DFN8 (4x4) mechanical dimensions



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Revision history ST1S30

7 Revision history

Table 9. Document revision history

Date	Revision	Changes
09-Sep-2010	1	First release

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